

Materials are classified as:

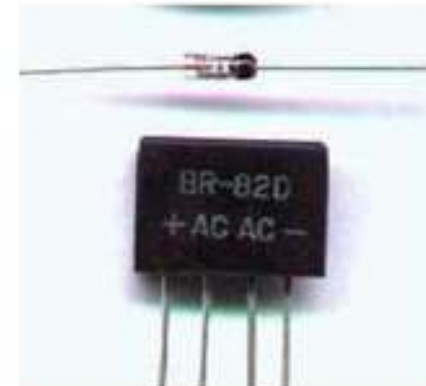
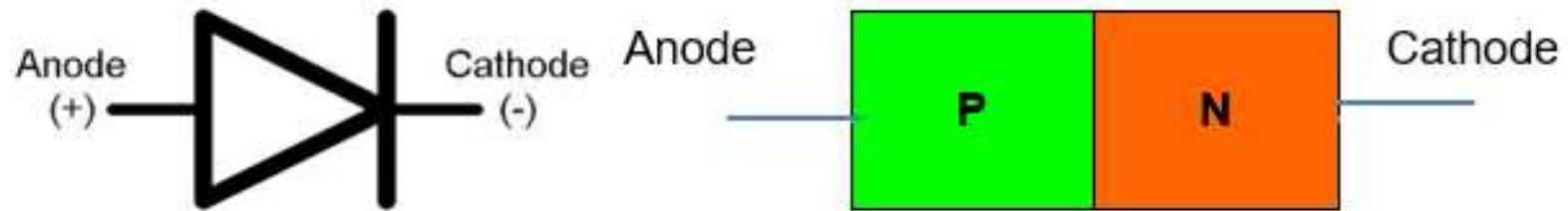
Conductors, Insulators and Semiconductors (Intrinsic and Extrinsic).

Drift and Diffusion Current:

When a conductor is subjected to an external voltage, free electrons move from (-)ve to (+)ve terminal with a steady velocity, constituting a current – **Drift Current**.

Diffusion Current- Due to diffusion phenomenon, due to flow of charge carriers from the region of higher concentration to the region of lower concentration.

P-N Junction Diode

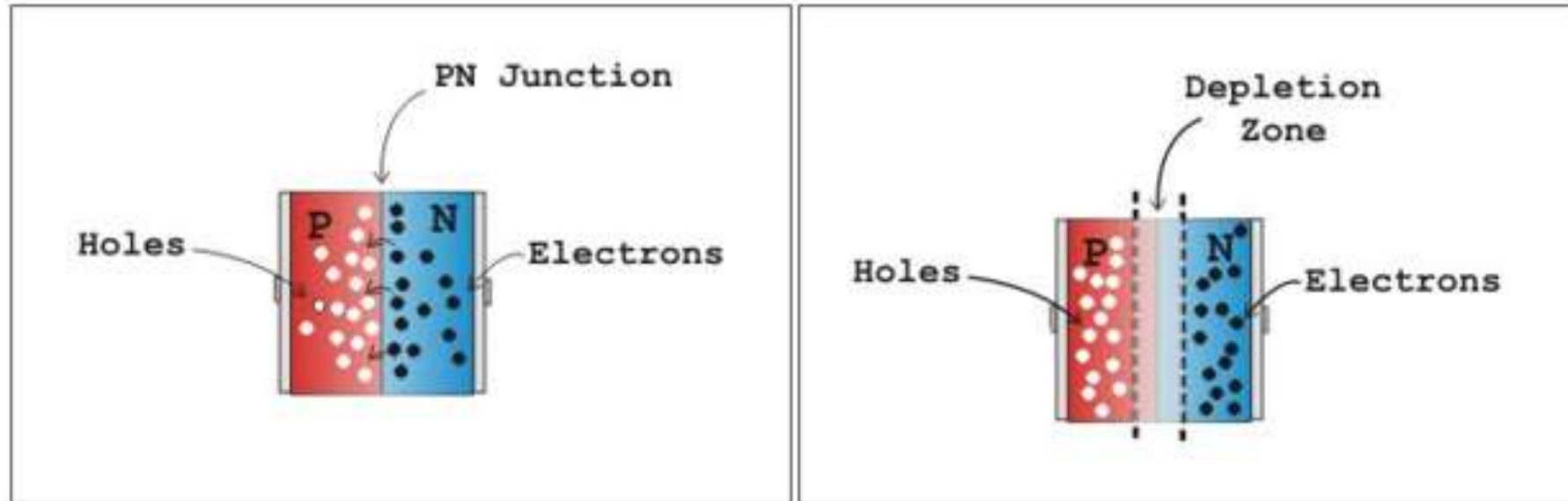


Common practical diodes available in market

Used in numerous applications

- ❖ Switch,
- ❖ Rectifier,
- ❖ Regulator,
- ❖ Voltage multiplier,
- ❖ Clipping,
- ❖ Clamping, etc.

P-N Junction Diode- conti...

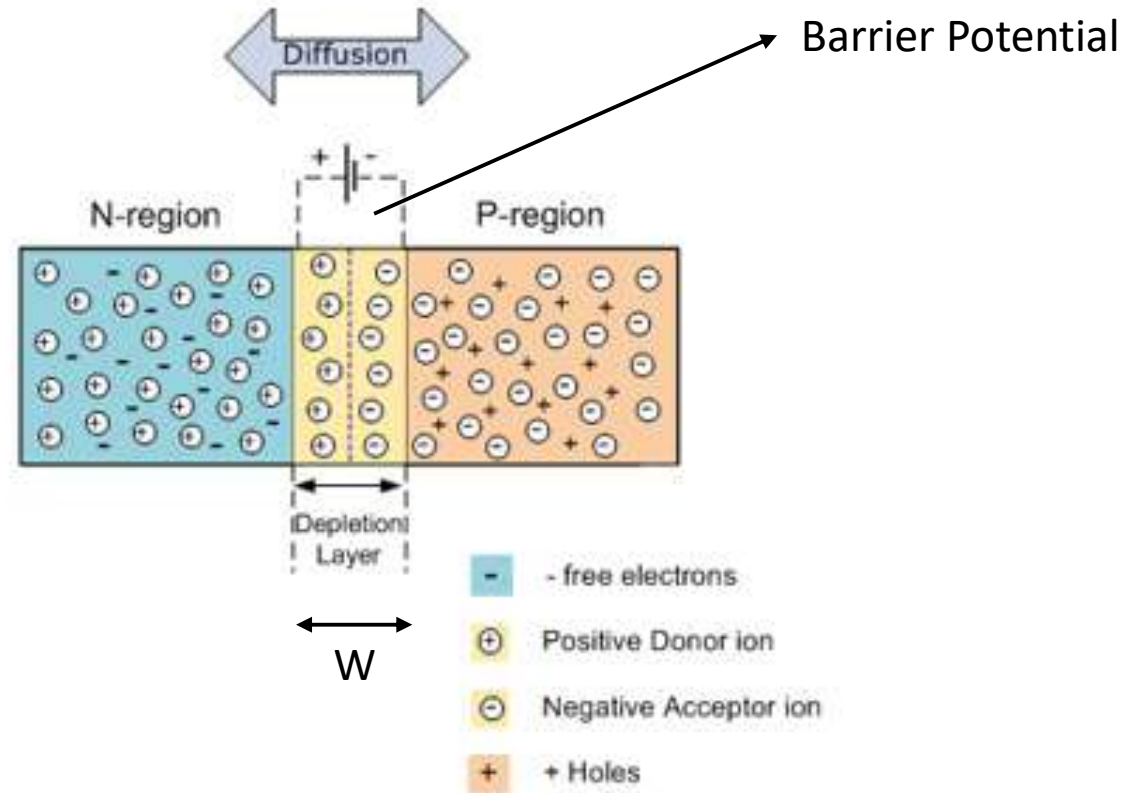


P-N junction (a) in contact (b) formation of depletion region

[<http://www.imagesco.com/articles/photovoltaic/photovoltaic-pg3.html>].

P-N Junction Diode under Zero bias condition

Unbias condition

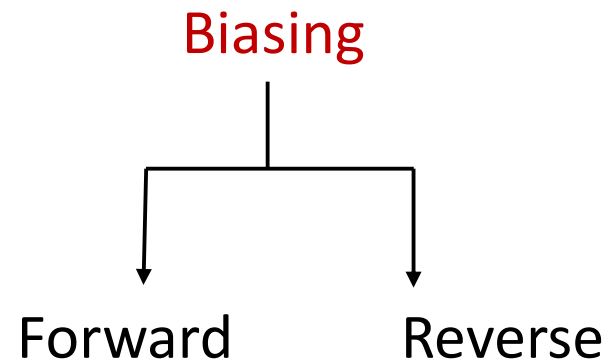


Diode under zero bias condition

Biasing: Applying external voltage to any electronic device

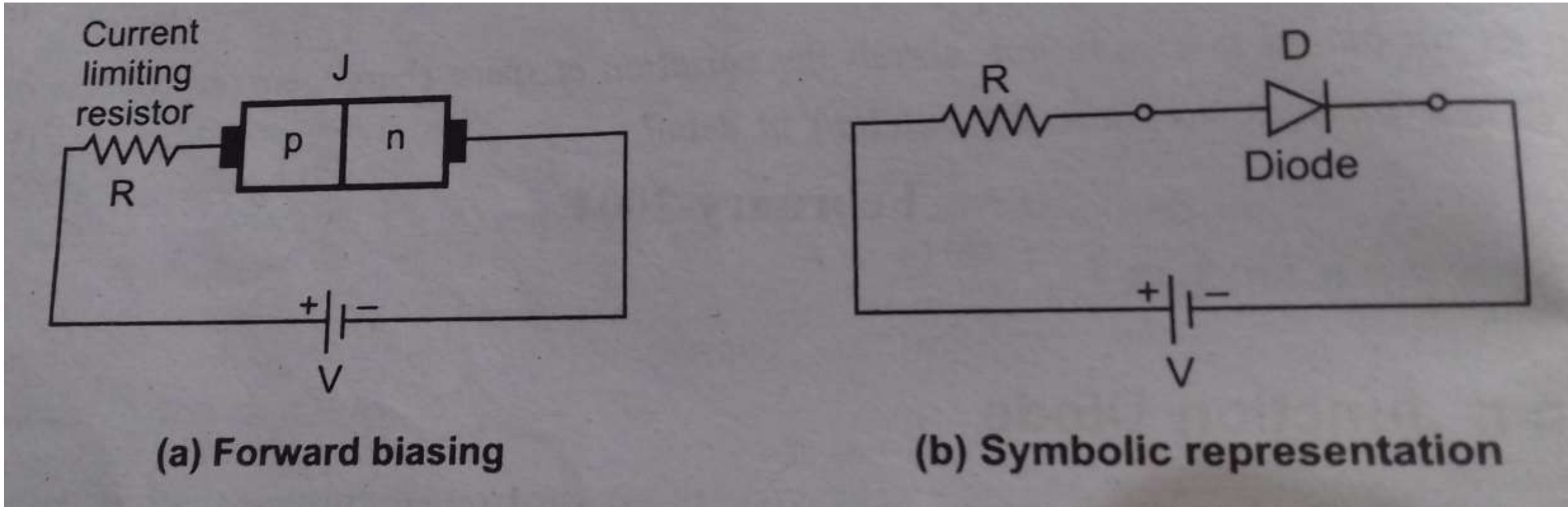
there is no current flow in the un biased P-N junction diode

Biasing allows current flow only in one direction

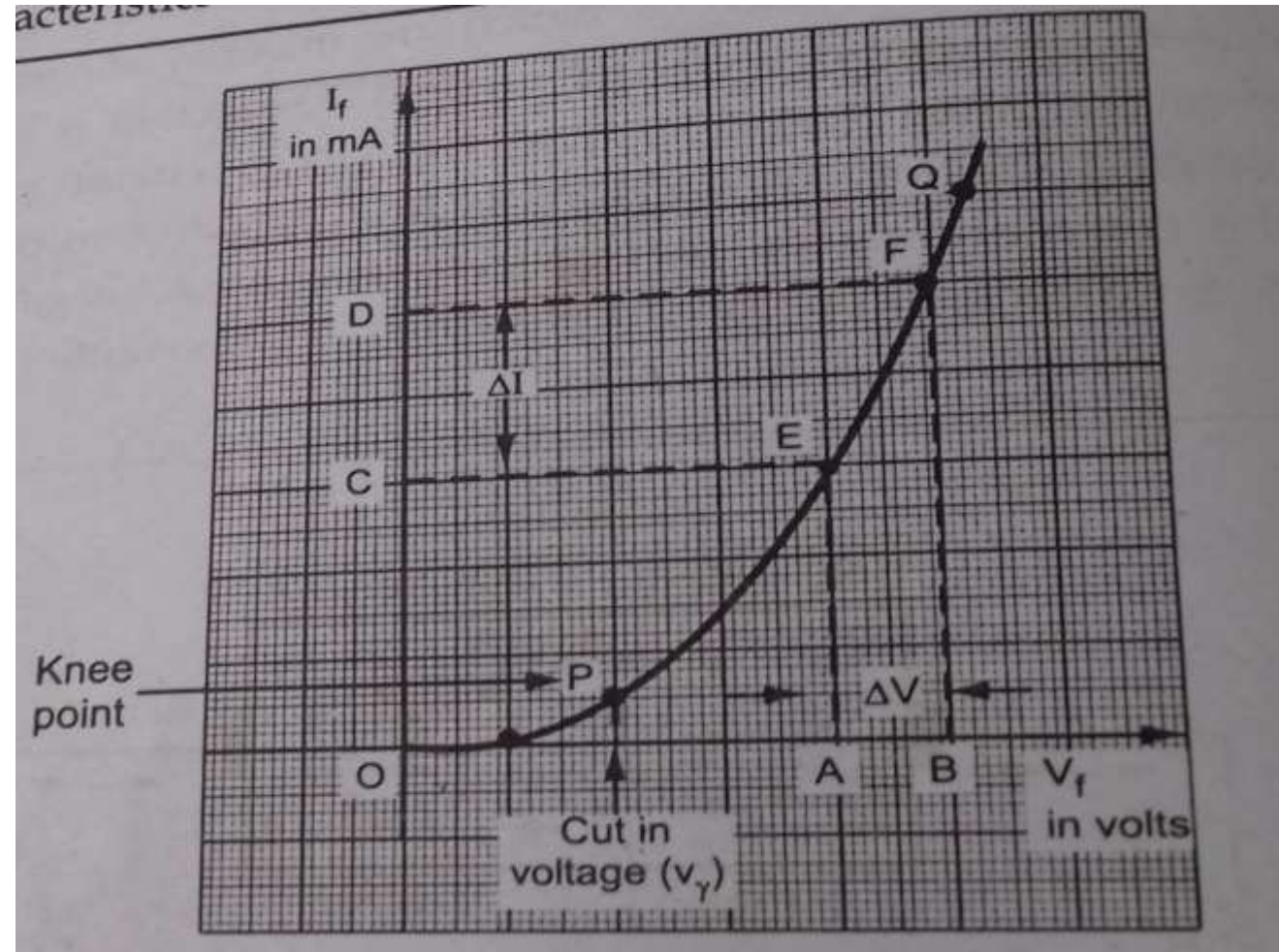
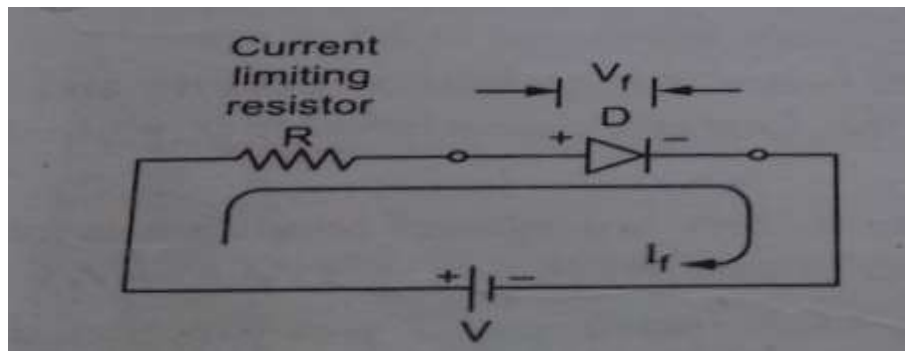
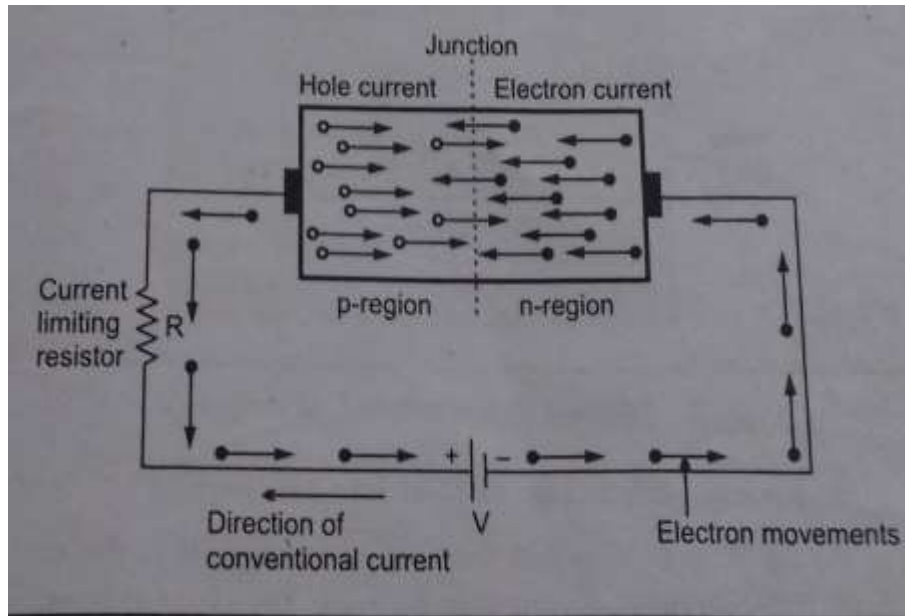


Forward bias

- Positive of battery connected to p-type (anode)
- Negative of battery connected to n-type (cathode)



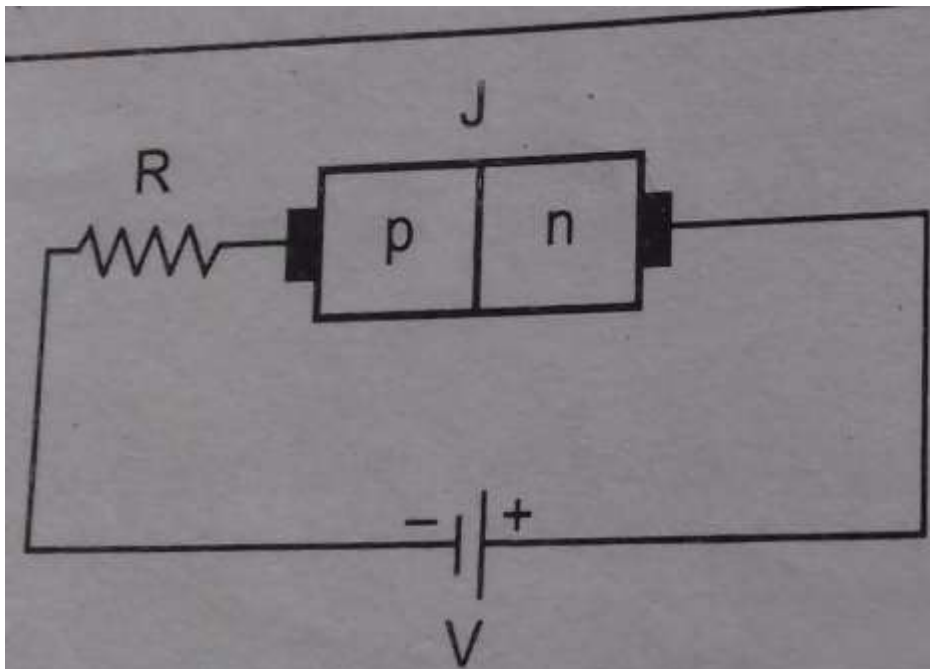
Forward bias



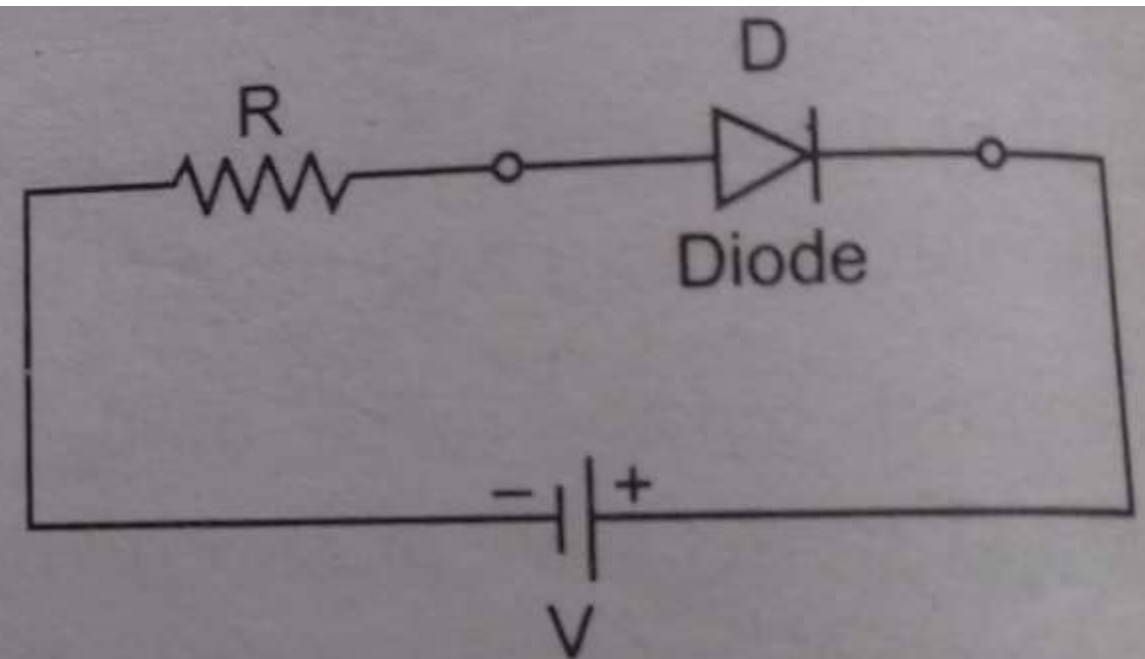
Forward Characteristics

Reverse bias

- Positive of battery connected to n-type material (cathode)
- Negative of battery connected to p-type material (anode)

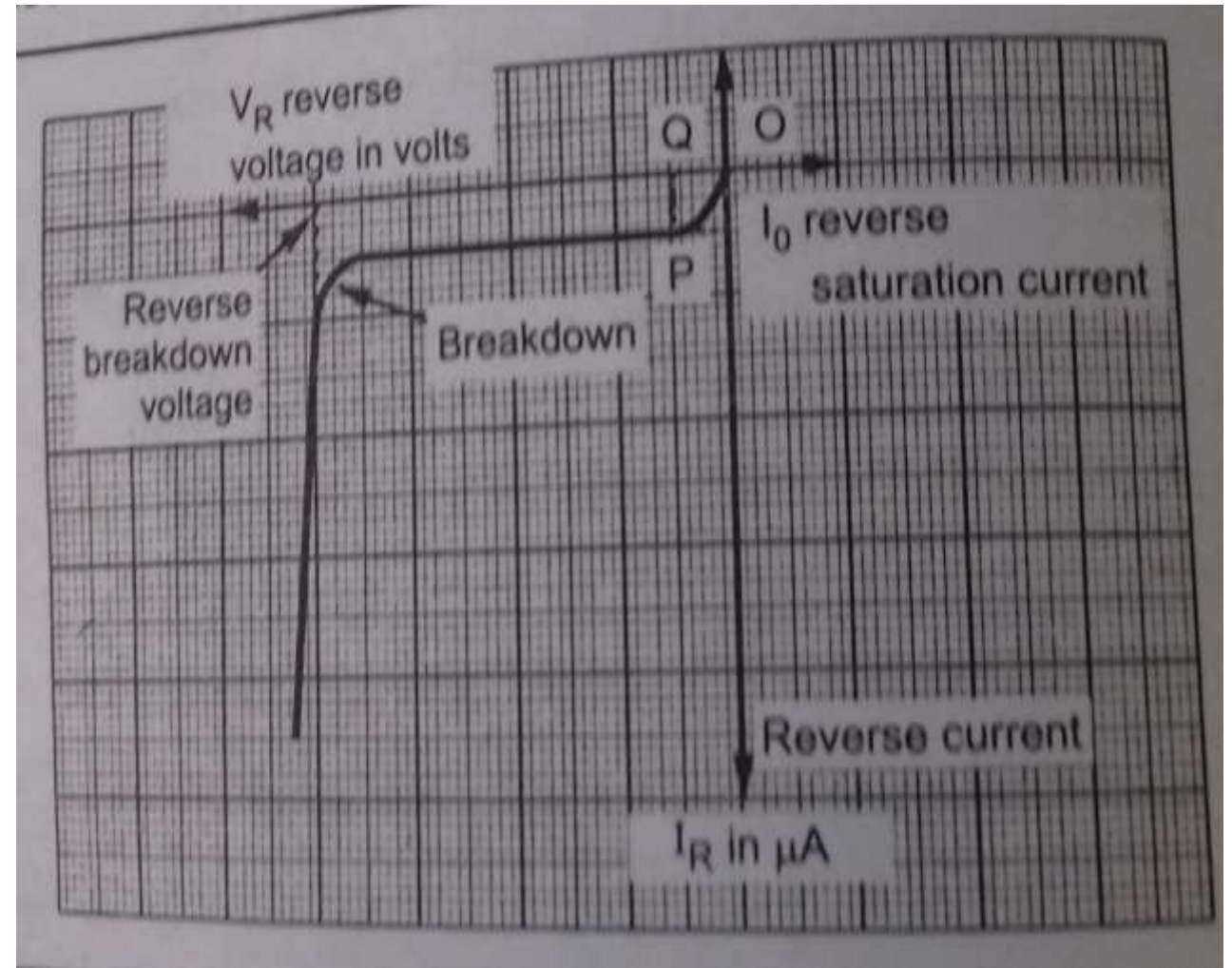
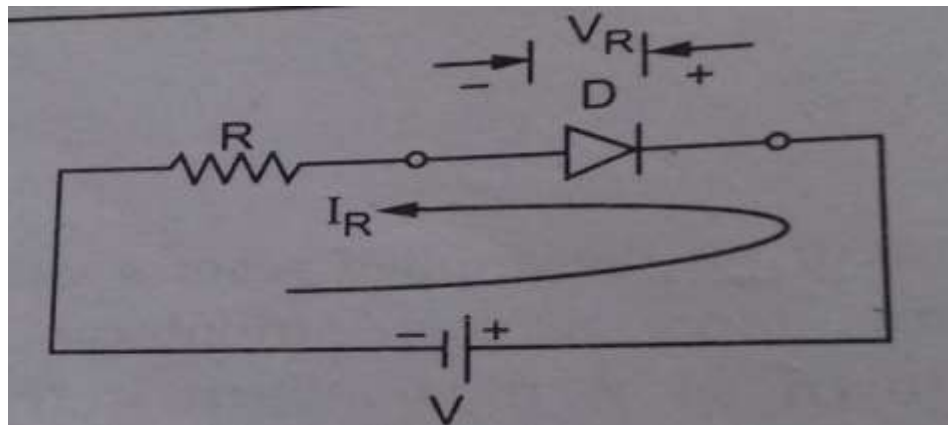
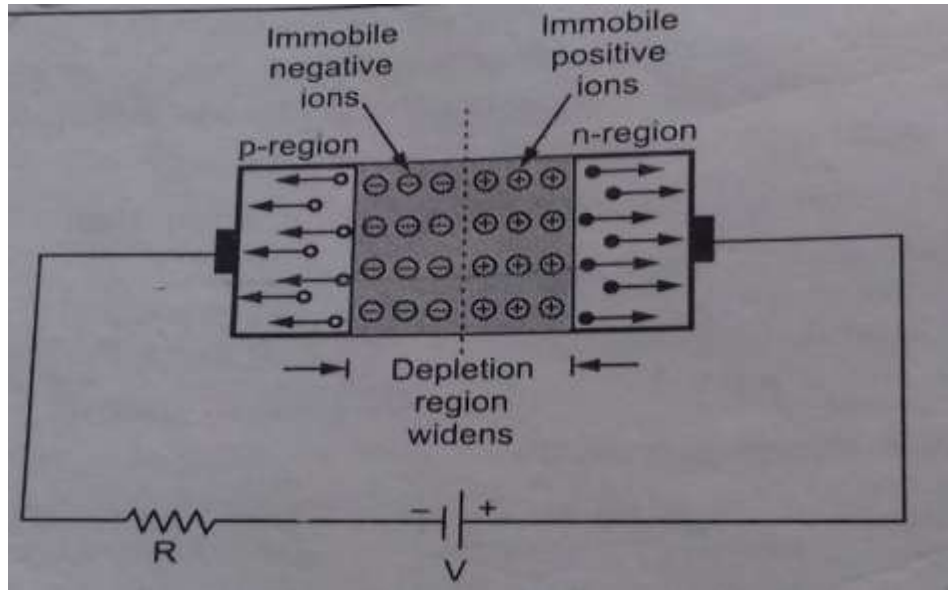


(a) Reverse biasing



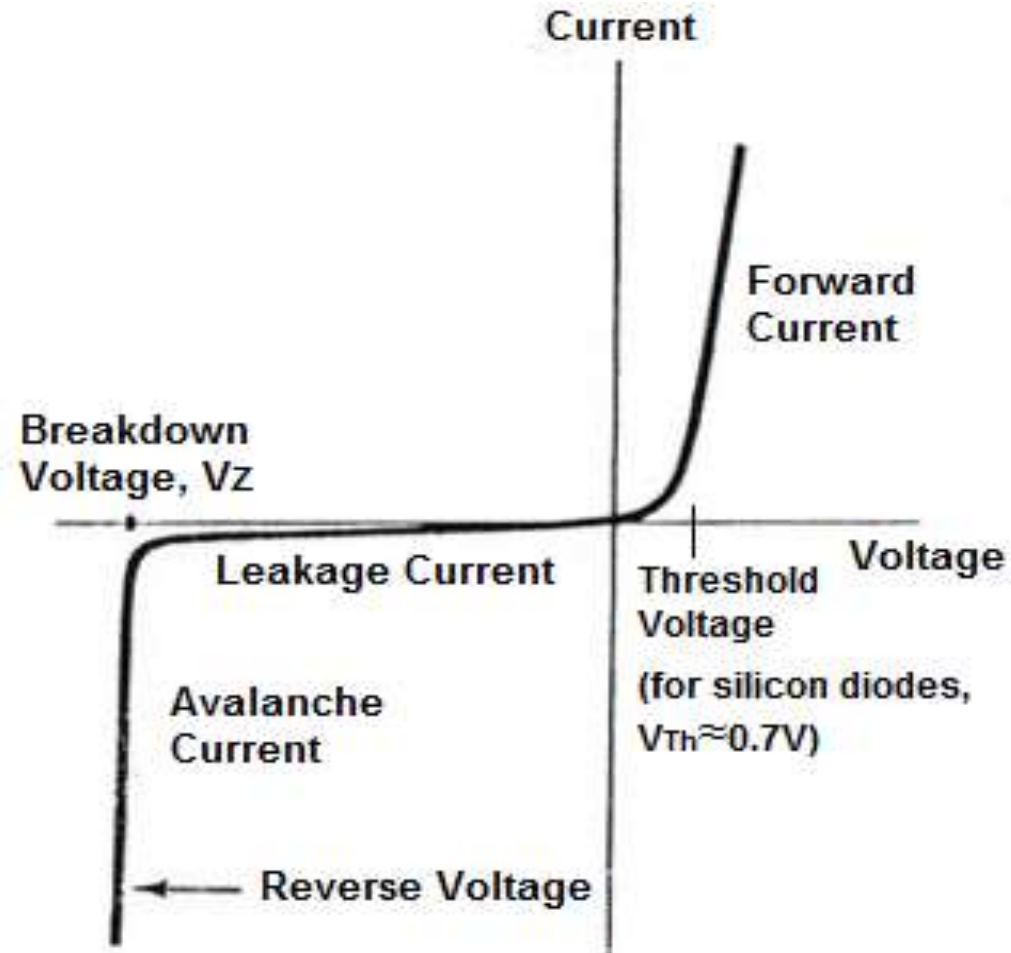
(b) Symbolic representation

Reverse bias



Reverse Characteristics

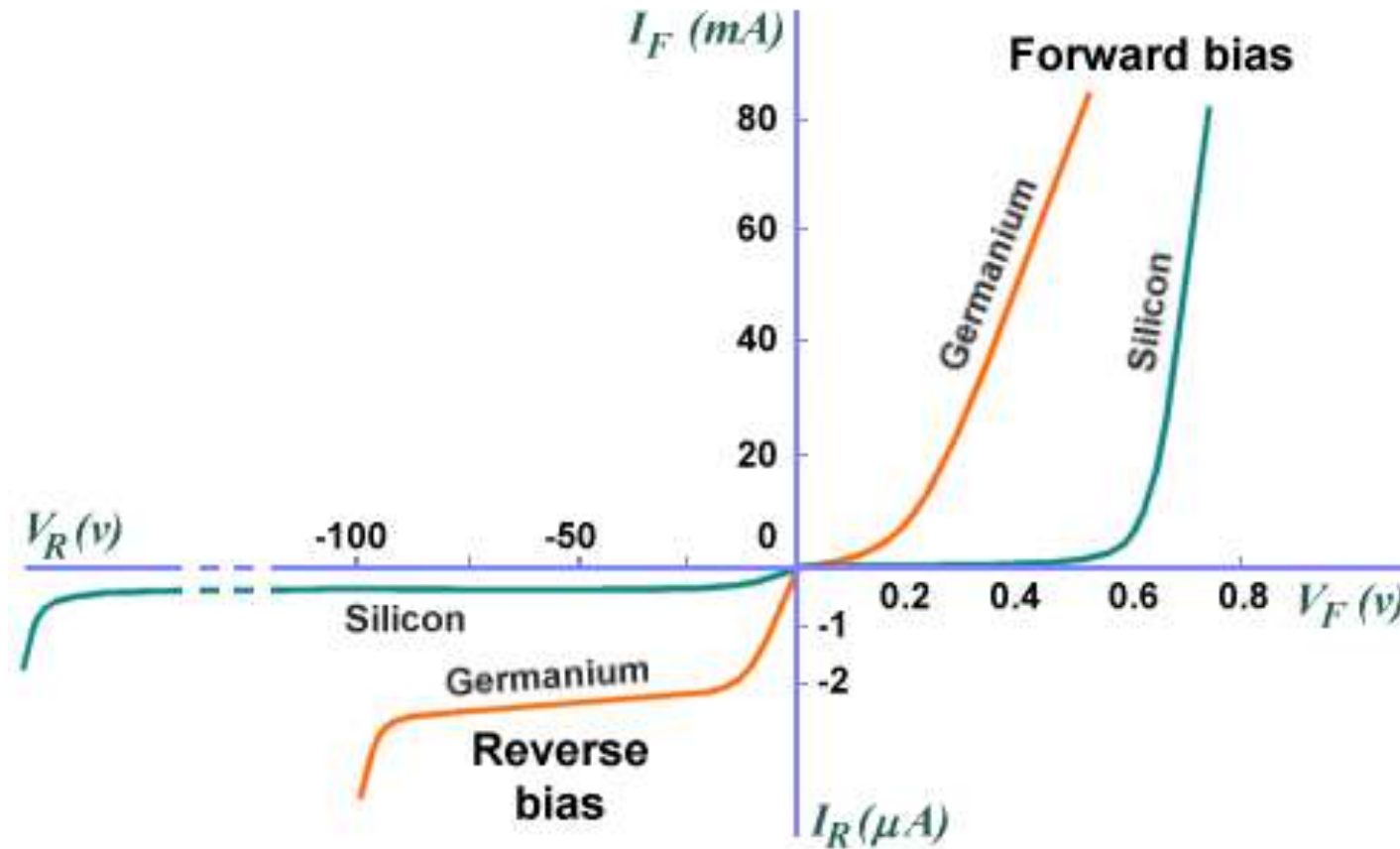
V-I characteristic of diode



V_γ is 0.6 ~ 0.7 V for Si
0.2 ~ 0.3 V for Ge

V-I characteristic of diode

Silicon (vs) Germanium



V-I characteristic of silicon and germanium practical diode

http://www.technologyuk.net/physics/electrical_principles/the_diode.shtml